



64K x 16 Static RAM

Features

- **High speed**
— $t_{AA} = 12 \text{ ns}$
- **CMOS for optimum speed/power**
- **Low active power**
— 1020 mW
- **Available in 450 x 550-mil LCC**
- **Automatic power-down when deselected**
- **Easy memory expansion with \overline{CE}_1 , \overline{CE}_2 , and \overline{OE} options**

Functional Description

The CY7C1021 is a high-performance CMOS static RAM organized as 65,536 words by 16 bits. Easy memory expansion is provided by an active LOW chip enable (\overline{CE}), an active LOW output enable (\overline{OE}), and three-state drivers. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

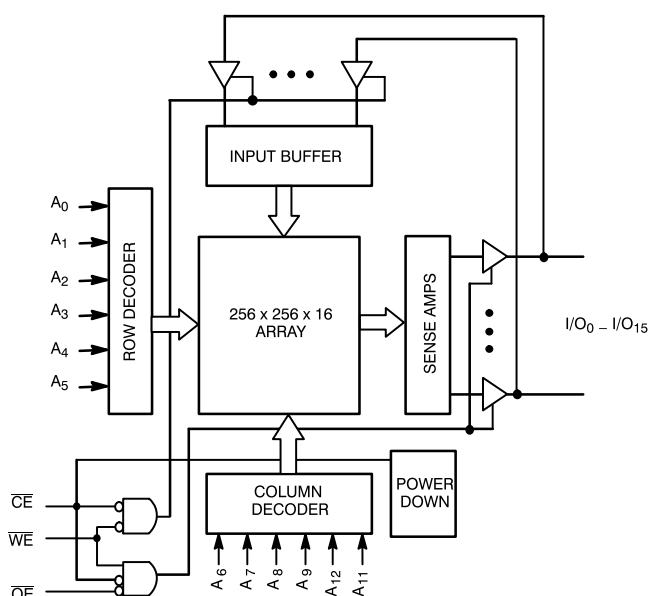
Writing to the device is accomplished by taking chip enable (\overline{CE}) and byte write enable ($\overline{BWE}/\overline{LBE}$) inputs LOW. Data on the appropriate eight I/O pins (I/O_0 through I/O_7 and/or I/O_8 through I/O_{15}) is then written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking chip enable (\overline{CE}) and output enable (\overline{OE}) LOW while forcing the write enables (\overline{BWE} and/or \overline{LBE}) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the appropriate I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected (\overline{CE} HIGH), the outputs are disabled (\overline{OE} HIGH), or during a write operation (\overline{CE} LOW, and \overline{WE} LOW).

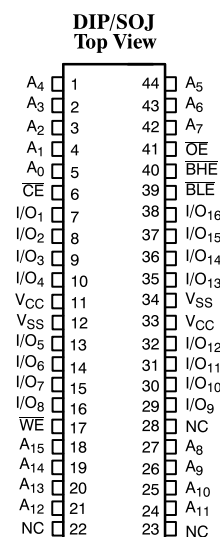
The CY7C1021 is available in standard 400-mil-wide DIPs and SOJs.

Logic Block Diagram



1021-1

Pin Configurations



1021-2

Selection Guide

		7C1021-12	7C1021-15	7C1021-20
Maximum Access Time (ns)		12	15	20
Maximum Operating Current (mA)	Commercial	195	180	165
	Military		195	180

Document #: 38-00224